Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 100 mΩ

3. Applications

- High-side load switch and charging switch for portable devices
- Power management in battery driven portables
- LED driver
- DC-to-DC converter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-2.4	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 °C		-	100	120	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



30 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D I
2	S	source	누ᆜ	
3	D	drain	4 3	$G \left(\begin{array}{c} \downarrow \\ \downarrow \downarrow \\ \downarrow \downarrow \end{array} \right)$
4	D	drain	Transparent top view DFN1010D-3 (SOT1215)	S 017aaa259

6. Ordering information

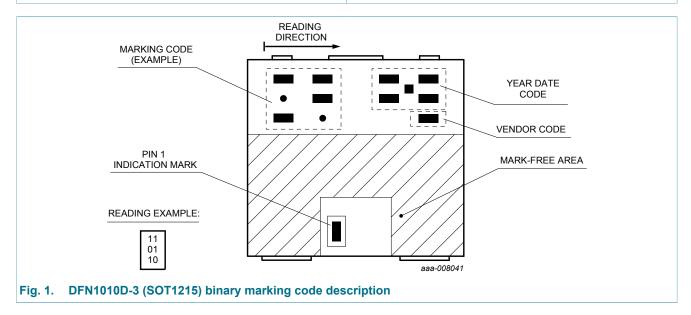
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMXB120EPE	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB120EPE	10 01 00



PMXB120EPE

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30 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-2.4	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-1.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-10	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	0.4	W
			[1]	-	1.07	W
		T _{sp} = 25 °C		-	8.33	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	diode					,
Is	source current	T _{amb} = 25 °C	[1]	-	-0.9	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

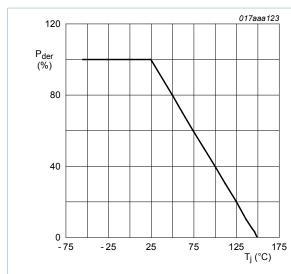


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

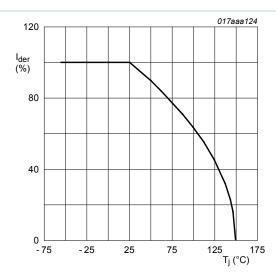


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMXB120EPE

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30 V, P-channel Trench MOSFET

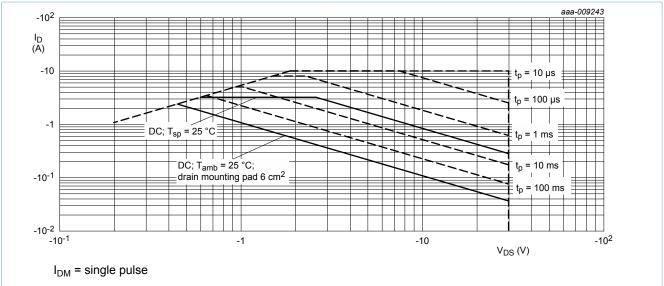


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

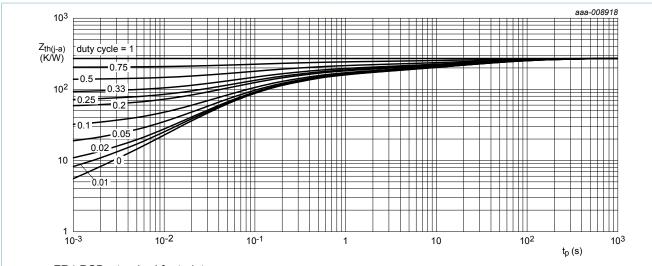
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	271	312	K/W
			[2]	-	102	117	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

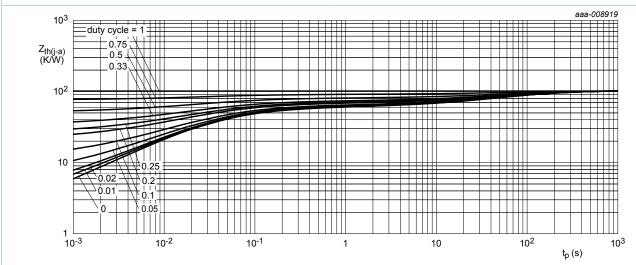
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

30 V, P-channel Trench MOSFET



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain $6\ \mathrm{cm}^2$

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, P-channel Trench MOSFET

10. Characteristics

Table 7 Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
racteristics		'	'		
drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-1	-1.5	-2.5	V
drain leakage current	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
	V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
drain-source on-state	V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 °C	-	100	120	mΩ
resistance	V _{GS} = -10 V; I _D = -2.4 A; T _j = 150 °C	-	156	187	mΩ
	V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C	-	125	170	mΩ
forward transconductance	V_{DS} = -10 V; I_D = -2.4 A; T_j = 25 °C	-	5	-	S
gate resistance	f = 1 MHz	-	14.5	-	Ω
characteristics		'			
total gate charge	V_{DS} = -15 V; I_{D} = -2.4 A; V_{GS} = -10 V;	-	6.2	11	nC
gate-source charge	T _j = 25 °C	-	0.9	-	nC
gate-drain charge		-	1.1	-	nC
input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	309	-	pF
output capacitance	T _j = 25 °C	-	41	-	pF
reverse transfer capacitance		-	32	-	pF
turn-on delay time	V _{DS} = -15 V; I _D = -2.4 A; V _{GS} = -10 V;	-	4	-	ns
rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	11	-	ns
turn-off delay time		-	16	-	ns
fall time		-	7	-	ns
ain diode		l	1	1	
source-drain voltage	$I_S = -0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance gate resistance total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time ain diode	racteristics drain-source breakdown voltage gate-source threshold voltage drain leakage current $V_{DS} = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 ^{\circ}C$ gate leakage current $V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ $V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 ^{\circ}C$ $V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 ^{\circ}C$ forward transconductance gate resistance $V_{DS} = -10 V; I_D = -2.4 A; T_j = 25 ^{\circ}C$ $V_{DS} = -10 V; I_D = -2.4 A; T_j = 25 ^{\circ}C$ $V_{DS} = -10 V; I_D = -2.4 A; T_j = 25 ^{\circ}C$ $V_{DS} = -10 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -10 V; V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V; V_{DS} = -10 $	racteristics drain-source breakdown voltage $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -30 gate-source threshold voltage $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ -1 drain leakage current gate leakage current $V_{DS} = -30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = 16 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -16 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = -2.4 \ A; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -4.5 \ V; \ I_D = -2.4 \ A; \ T_j = 25 \ ^{\circ}C$ - $V_{DS} = -10 \ V; \ I_D = -2.4 \ A; \ T_j = 25 \ ^{\circ}C$ - $V_{DS} = -10 \ V; \ I_D = -2.4 \ A; \ V_{GS} = -10 \ V;$ - $V_{DS} = -15 \ V; \ I_D = -2.4 \ A; \ V_{GS} = 0 \ V;$ - $V_{DS} = -15 \ V; \ I_D = -2.4 \ A; \ V_{GS} = 0 \ V;$ - $V_{DS} = -15 \ V; \ I_D = -2.4 \ A; \ V_{GS} = 0 \ V;$ - $V_{DS} = -15 \ V; \ I_D = -2.4 \ A; \ V_{GS} = -10 \ V;$ -	tracteristics drain-source breakdown voltage $I_D = -250 \mu A; V_{GS} = 0 V; T_J = 25 ^{\circ}C$ -30 - gate-source threshold voltage $I_D = -250 \mu A; V_{DS} = V_{GS}; T_J = 25 ^{\circ}C$ -1 -1.5 drain leakage current voltage $V_{DS} = -30 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - gate leakage current voltage $V_{GS} = 16 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - $V_{GS} = -16 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - - $V_{GS} = -10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - $V_{GS} = -10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - $V_{GS} = -10 V; V_{DS} = 0 V; T_J = 25 ^{\circ}C$ - - $V_{GS} = -10 V; I_D = -2.4 A; T_J = 25 ^{\circ}C$ - 100 $V_{GS} = -4.5 V; I_D = -2.4 A; T_J = 25 ^{\circ}C$ - 5 fonward transconductance gate resistance f = 1 MHz - 14.5 tharacteristics total gate charge gate-drain charge $V_{DS} = -15 V; I_D = -2.4 A; V_{GS} = -10 V;$ - 6.2 gate-drain charge	drain-source breakdown voltage I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C -30 - - gate-source threshold voltage I _D = -250 μA; V _{DS} = V _{GS} ; T _j = 25 °C -1 -1.5 -2.5 drain leakage current voltage V _{DS} = -30 V; V _{DS} = 0 V; T _j = 25 °C - - -1 gate leakage current voltage V _{DS} = -30 V; V _{DS} = 0 V; T _j = 25 °C - - -10 V _{SS} = 16 V; V _{DS} = 0 V; T _j = 25 °C - - -10 V _{SS} = 10 V; V _{DS} = 0 V; T _j = 25 °C - - -10 V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C - - -10 V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C - - -1 drain-source on-state resistance V _{GS} = -10 V; I _D = -2.4 A; T _j = 25 °C - - -10 V _{GS} = -10 V; I _D = -2.4 A; T _j = 25 °C - - 156 187 V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C - - 5 total gate charge f = 1 MHz - 14.5 - gate-drain charge routput capacitance - - -

6/15

30 V, P-channel Trench MOSFET

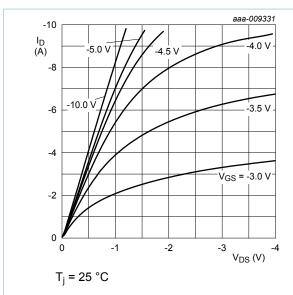


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

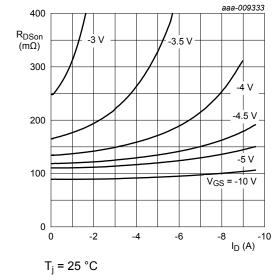


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

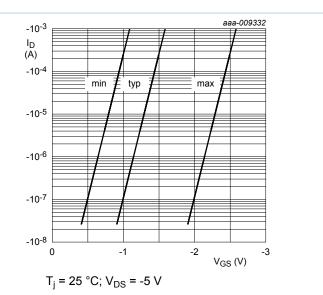


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

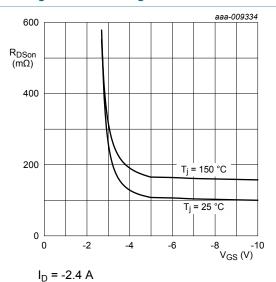


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V, P-channel Trench MOSFET

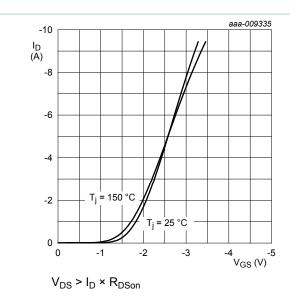


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

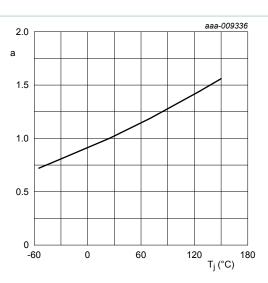


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

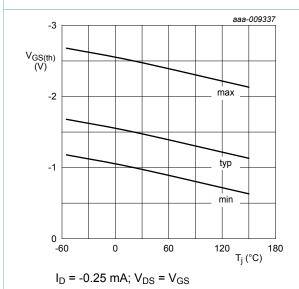


Fig. 13. Gate-source threshold voltage as a function of junction temperature

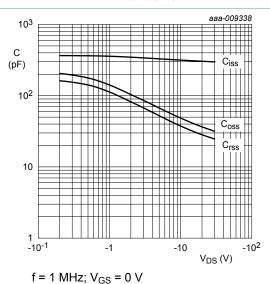


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

30 V, P-channel Trench MOSFET

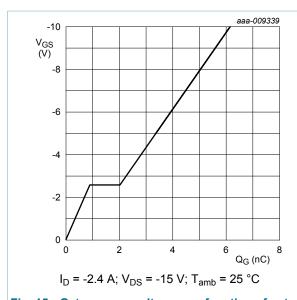


Fig. 15. Gate-source voltage as a function of gate charge; typical values

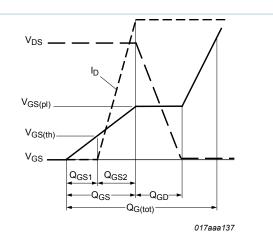


Fig. 16. MOSFET transistor: Gate charge waveform definitions

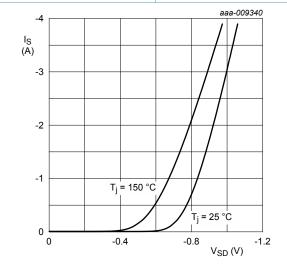
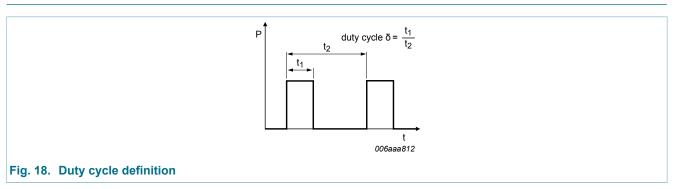


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

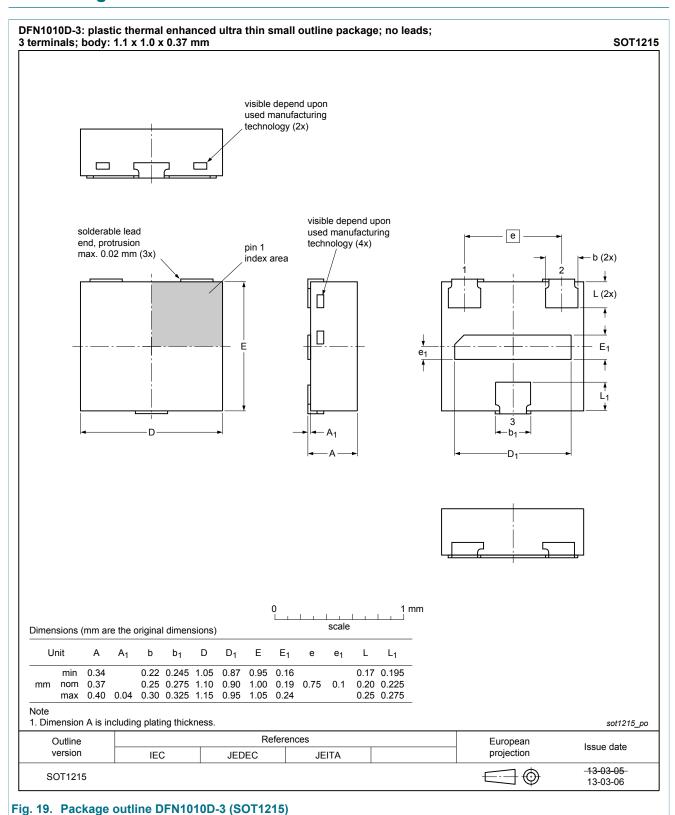


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12. Package outline

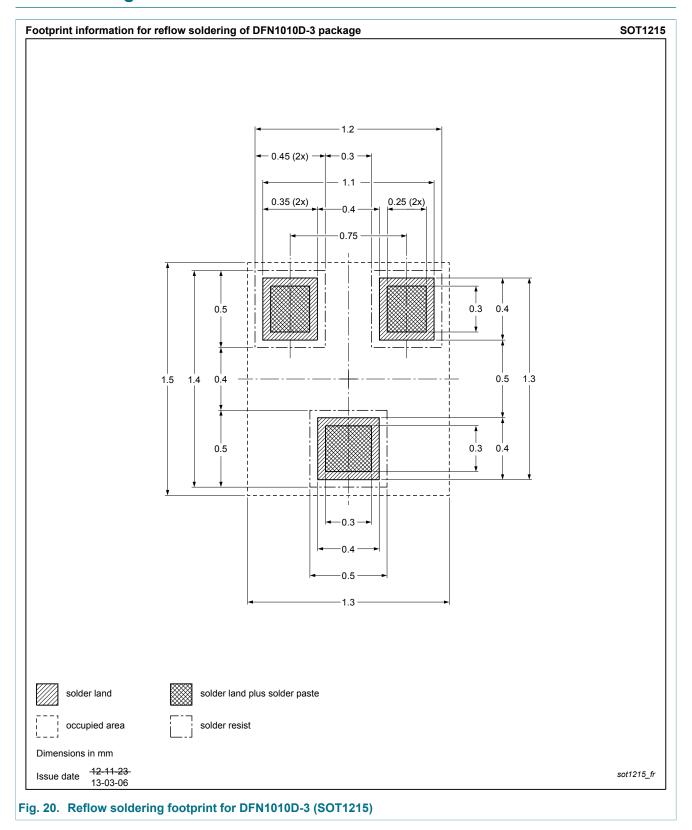


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30 V, P-channel Trench MOSFET

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB120EPE v.1	20130924	Product data sheet	-	-

30 V, P-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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30 V, P-channel Trench MOSFET

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30 V, P-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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